60 V, 360 mA N-channel Trench MOSFET

23 November 2020

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Logic-level compatible
- Very fast switching
- · Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- Relay driver
- · High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	-	60	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	360	mA
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 500 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.01; T_j = 25 °C		-	1	1.6	Ω

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain		G—(154)
			1 2	mbb076 S
			SOT23	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
2N7002P	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
2N7002P	LW%

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	360	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	280	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	1.2	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	350	mW
			[1]	-	420	mW
		T _{sp} = 25 °C		-	1140	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode		'	'		
Is	source current	T _{amb} = 25 °C	[1]	-	360	mA

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

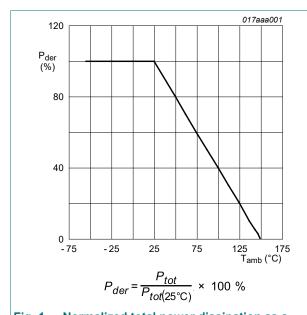


Fig. 1. Normalized total power dissipation as a function of ambient temperature

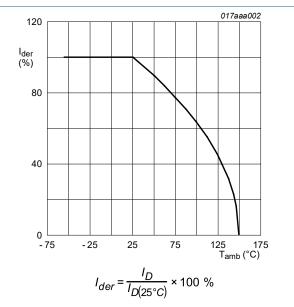
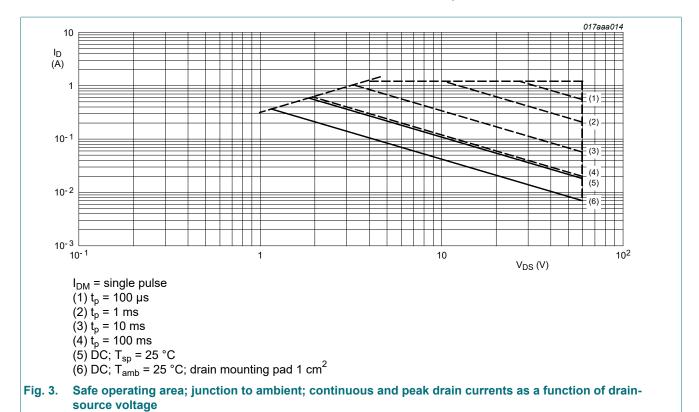


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	310	370	K/W
junction to ambier	junction to ambient		[2]	-	260	300	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	115	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

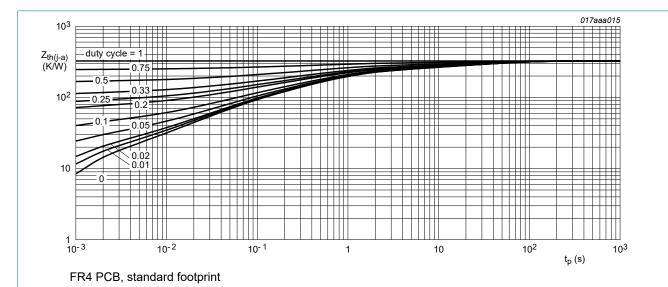
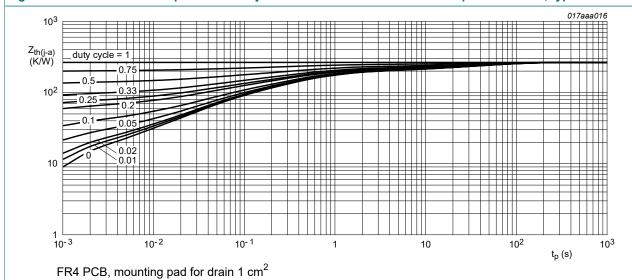


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 10 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.75	2.4	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon} drain-source on-state resistance		V_{GS} = 5 V; I_{D} = 50 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.01; T_{j} = 25 °C	-	1.3	2	Ω
	V_{GS} = 10 V; I_D = 500 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.01; T_j = 25 °C	-	1	1.6	Ω	
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 200 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.01; T_{j} = 25 °C	-	400	-	mS
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = 30 \text{ V}; I_D = 300 \text{ mA}; V_{GS} = 4.5 \text{ V};$	-	0.6	0.8	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.2	-	nC
Q _{GD}	gate-drain charge		-	0.2	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	30	50	pF
C _{oss}	output capacitance	T _j = 25 °C	-	7	-	pF
C _{rss}	reverse transfer capacitance	_	-	4	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 250 \Omega; V_{GS} = 10 \text{ V};$	-	3	6	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	4	-	ns
t _{d(off)}	turn-off delay time		-	10	20	ns
t _f	fall time		-	5	-	ns
Source-dra	in diode					
V_{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V; T _j = 25 °C	0.47	0.75	1.1	V
				_	_	

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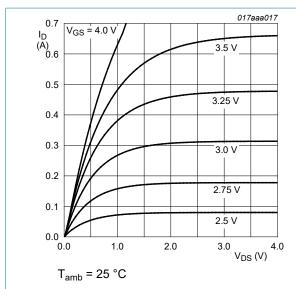
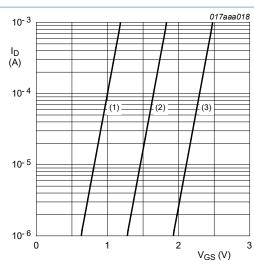


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



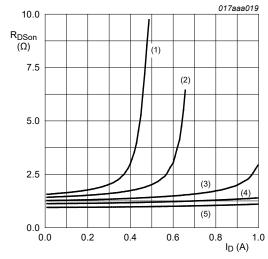
 T_{amb} = 25 °C; V_{DS} = 5 V (1) minimum values

(2) typical values

(3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

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 T_{amb} = 25 °C

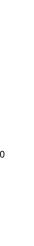
(1) $V_{GS} = 3.25 \text{ V}$

 $(2) V_{GS} = 3.5 V$

(3) $V_{GS} = 4 V$ (4) $V_{GS} = 5 V$ $(5) V_{GS} = 10 V$

Drain-source on-state resistance as a function Fig. 8.

of drain current; typical values



6.0 $\mathsf{R}_{\mathsf{DSon}}$ (Ω) 4.0 (1) 2.0 (2) 0.0 0.0 2.0 8.0 10.0 V_{GS} (V)

 $I_D = 500 \text{ mA}$

(1) T_{amb} = 150 °C

 $(2) T_{amb} = 25 °C$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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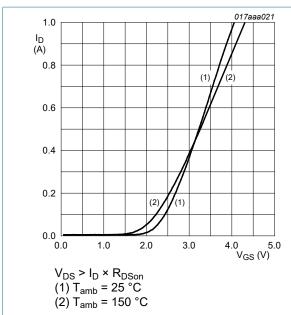


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

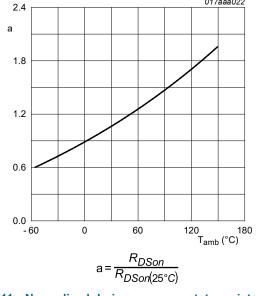
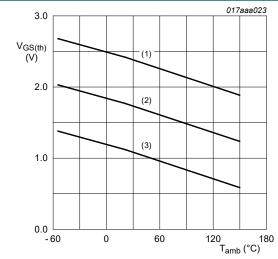


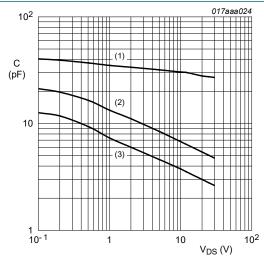
Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of ambient temperature



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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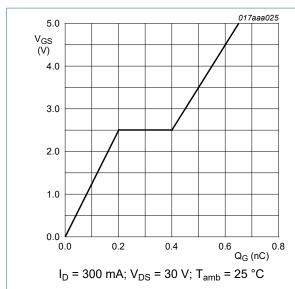


Fig. 14. Gate-source voltage as a function of gate charge; typical values

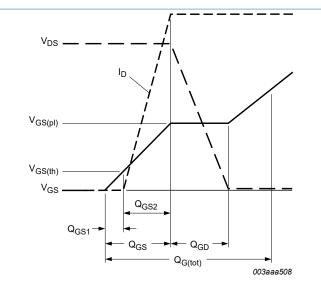
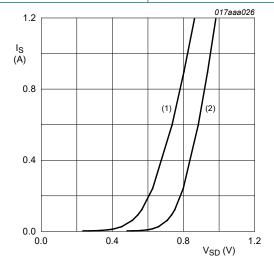


Fig. 15. Gate charge waveform definitions

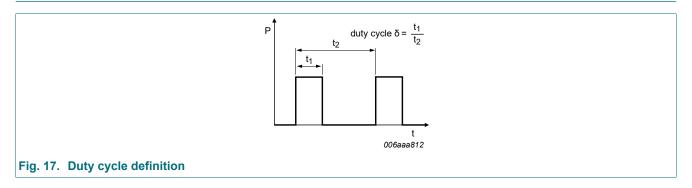


V_{GS} = 0 V (1) T_{amb} = 150 °C (2) T_{amb} = 25 °C

Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

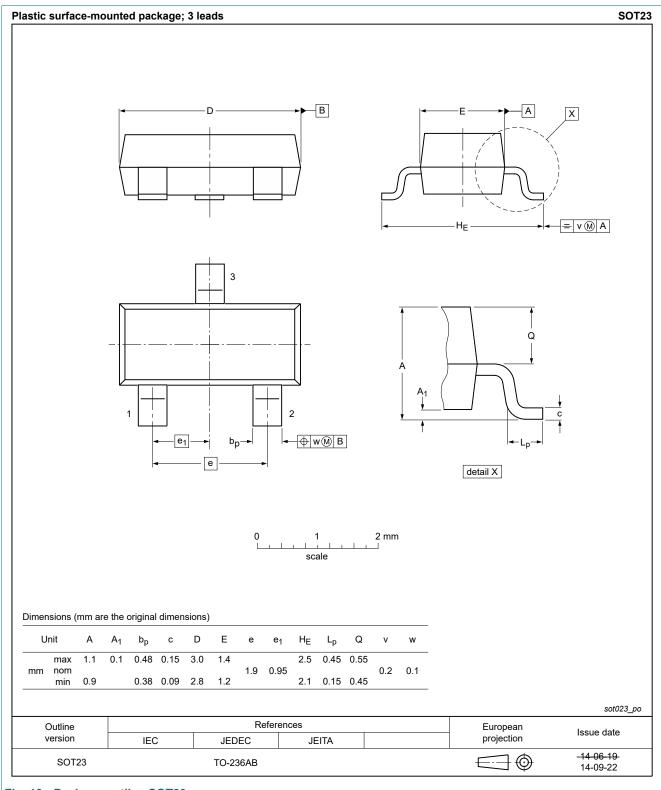
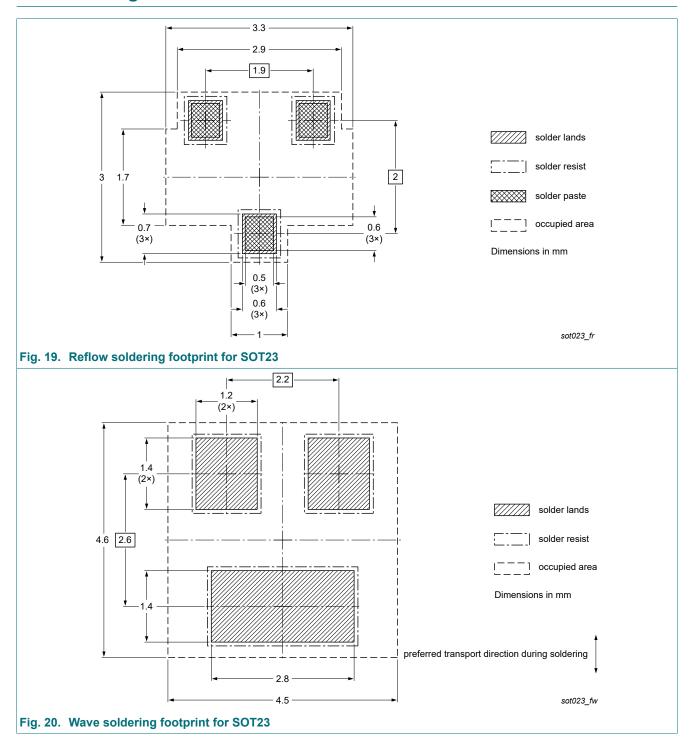


Fig. 18. Package outline SOT23

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13. Soldering



Product data sheet

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14. Revision history

Table 8. Revision history

Release date	Data sheet status	Change notice	Supersedes		
20201123	Product data sheet	-	2N7002P v.2		
 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Chapter "Characteristics": Typo correction for I_{GSS}. 					
20100729	Product data sheet	-	2N7002P v.1		
20100419	Product data sheet	-	-		
	The format of this da Nexperia. Legal texts have bee Chapter "Characteris 20100729	Product data sheet The format of this data sheet has been redesing Nexperia. Legal texts have been adapted to the new corest Chapter "Characteristics": Typo correction for 20100729 Product data sheet	Product data sheet The format of this data sheet has been redesigned to comply with the in Nexperia. Legal texts have been adapted to the new company name where approximately contact the new co		

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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